Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1277	(@ad<"20031204") and (polysilicon same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:44
L2	1101	L1 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 16:51
L3	890	L1 and (gate same (patterning or etch or etching or pattern))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:56
L4	606	(@ad<"20031204") and ((silicide and polysilicon) same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 20:25
L5	544	L4 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 16:51
L6	476	L4 and (gate same (patterning or etch or etching or pattern))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:06
L7	330	L6 and (tungsten or "w")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 16:55
L8	112	L7 and ("wn" or "tan"or "tin")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:24

L9	454	L4 and (silicide same (patterning or etch or etching or pattern))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:05
L10	426	L4 and ((polysilicon and silicide) same (patterning or etch or etching or pattern))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:05
L11	157	L4 and (((tungsten or "w") and polysilicon and silicide) same (patterning or etch or etching or pattern))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:36
L12	154	L11 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:15
L13	12	L11 and (("w" or tungsten) near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:16
L14	19643	l4 qand ("tisi" or "cosi" or "nisi" or "ptsi" or "tasi" or "hfsi" or "nisi")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:35
L15	100	l4 and ("tisi" or "cosi" or "nisi" or "ptsi" or "tasi" or "hfsi" or "nisi")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 17:35
L16	63	L15 and (tungsten or "w")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:25

L17	152	L1 and 438/581,583,587,591,592, 593,630,649,651,655,656,657,664, 682,721,755.ccls. and ("w" or tungsten)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:43
L18	147	L17 and (silicide or msi)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:23
L19	84	L17 and (barrier or "wn" or "tan"or "tin")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:24
L20	141	L17 and (barrier or "wn" or "tan"or "tin" or nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:24
L21	59	L20 and ((barrier or "wn" or "tan"or "tin" or nitride) with (tungsten or "w"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:26
L22	59	L21 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:26
L23	59	l22 and ((silicide or polysilicon) same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:33
L24	36	l22 and ((silicide or polysilicon) with (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:33

L25	3844	(@ad<"20031204") and 438/581, 583,587,591,592,593,630,649,651, 655,656,657,664,682,721,755.ccls. and ("w" or tungsten)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:43
L26	6678	(@ad<"20031204") and 438/581, 583,587,591,592,593,630,649,651, 655,656,657,664,682,721,755.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:43
L27	101	L26 and (rta or (rapid near anneal$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:52
L28	68	L27 and gate.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:45
L29	53	L28 and silicide.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:47
L30	28	L28 and (tungsten or "W").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:53
L31	23	L30 and silicide.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:47
L32	23	L26 and ((rta or (rapid near anneal$3)) with (polysilicon or silicide)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:52

L33	11	L32 and (gate and (tungsten or "W")).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:53
L34	1870	gate and ((patterning or etch or etching or pattern) with ((tungsten or "w") and (nitride or barrier) and silicide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 18:58
L35	24	L34 and ((silicide and polysilicon) same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 19:00
L36	126	L34 and ((silicide or metal or polysilicon) same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 19:01
L37	127	L34 and ((silicide or metal or polysilicon or polycide) same (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 20:22
L38	1	("6514841").PN.	USPAT; USOCR	OR	OFF	2005/08/30 20:25
L39	47	L4 and (("nitrogen ambient") with (rta or (rapid near anneal$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 20:26